

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>		
Sheet		1	of	2	Application Number	<u>10/1566522</u>
					Filing Date	10/15/2005
					First Named Inventor	Yesbito Jin
					Art Unit	10566522 - GAU: 2894
					Examiner Name	/Jami Valentine/
					Attorney Docket Number	096790.P520

U.S. PATENT DOCUMENT					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US 3,795,977		3/12/1974	Berkenflit et al.
		99			
		US			

FOREIGN PATENT DOCUMENT

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	KindCode ⁵ (if known)			
		JP	08-031960	A	02-02-1996	MATSUSHITA ELECTRIC IND CO LTD	Abstract
		JP	10-152397	A	06-09-1998	NIPPON TELEGRAPH & TELEPHONE CORP	Abstract
		JP	10-152398	A	06-09-1998	NIPPON TELEGR & TELEPH CORP	Abstract
		JP	2003-077911	A	03-14-2003	NIPPON TELEGR & TELEPH CORP	Abstract
		JP	2814416	B	08-14-1998	NIPPON TELEGR & TELEPH CORP	Abstract
		JP	2779997	B	05-15-1998	NIPPON TELEGR & TELEPH CORP	Abstract
		JP	08-306806	A	11-22-1996,	ASAHI CHEM IND CO LTD	Abstract
		JP	07-263646	A	10-13-1995	MITSUBISHI CHEM CORP	Abstract
		JP	08-161933	A	06-21-1996	SHARP CORP	Abstract
		JP	50-004986	A	01-20-1975	INTERNATIONAL BUSINESS MACHINES CORP	
		JP	49-034390	B	09-13-1974	MATSUSHITA ELECTRIC IND CO LTD	Abstract

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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /JMV/

Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i> 10/566522	
Sheet	2	of	2	Application Number	10566522 - GAU: 2894
				Filing Date	
				First Named Inventor	Yoshito Jin
				Art Unit	
				Examiner Name	/Jami Valentine/
				Attorney Docket Number	096790.P520

OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		Translation ²
	Sze, "Physics of Semiconductor Devices", Jhon Wiley and Sons, Inc., 1981			
	Matsuoka, "Applied Physics", Vol. 73, No. 9, pp.1166, 2004			Abstract
	"Development and Application of Ferroelectric Materials", edited by Tadashi Shiosaki, CMC Co., Ltd.			Abstract
	Inomata et al., "MRM Technology - from Fundamentals to LSI Applications", SIPEC			Abstract
	Amazawa et al., "Ultrathin oxidefilms deposited using electron cyclotron resonance sputter", J. Vac. Sci. Technol. B 17, No. 5			
	Matsuoka et al., "Low-temperature epitaxial growth of BaTiO ₃ films by radio-frequency-mode electron cyclotron resonance sputtering", J. Appl. Phys., 76(3), 1768 (1994)			
	Watazu et al., "Powder and Powder Metallurgy", No. 44, pp. 86, 1997			Abstract
	Masumoto et al., "Preparation of Bi ₄ Ti ₃ O ₁₂ films on a single-crystal sapphire substrate with electron cyclotron resonance plasma sputtering", Appl. Phys. Lett., 58, 243 (1991)			
	Yamaguchi et al., "Effect of Grain Size on Bi ₄ Ti ₃ O ₁₂ Thin Film Properties", Jpn. J. Appl. Phys., Vol. 37, (1998) pp. 5166 - 5170			
	Wild et al., "Hafnium and Zirconium silicates for advanced gate dielectrics", J. Appl. Phys., Vol. 87, No. 1, January 2000, pp. 484 - 492			

Examiner Signature	/Jami Valentine/	Date Considered	12/17/2008
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